# DISCRETE SEMICONDUCTORS

# DATA SHEET

PMBF4391; PMBF4392; PMBF4393

N-channel FETs

**Product specification** 

**April 1995** 



# **N-channel FETs**

# PMBF4391; PMBF4392; PMBF4393

# **DESCRIPTION**

Symmetrical silicon n-channel depletion type junction field-effect transistors on a plastic microminiature envelope intended for application in thick and thin-film circuits. The transistors are intended for low-power chopper or switching applications in industry.

# **PINNING**

1 = drain

2 = source

3 = gate

### Note

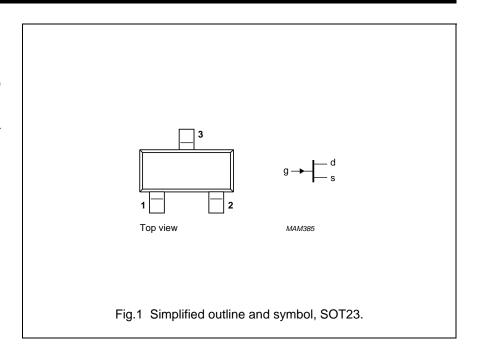
1. Drain and source are interchangeable.

# Marking code

PMBF4391 = p6J

PMBF4392 = p6K

PMBF4393 = p6G



# **QUICK REFERENCE DATA**

		PMBF4391		PMBF4392 PMBF4		F4393
Drain-source voltage	$\pm \ V_{DS}$	max.	40	40	40	V
Drain current						
$V_{DS} = 20 \text{ V}; V_{GS} = 0$	$I_{DSS}$	>	50	25	5	mA
Gate-source cut-off voltage						
$V_{DS} = 20 \text{ V; } I_D = 1 \text{ nA}$	-V <sub>(P)GS</sub>	>	4	2	0.5	V
VDS = 20 V, ID = 1 IIA	−v(P)GS	<	10	5	3	V
Drain-source resistance (on) at f = 1 kHz						
$I_D = 0; V_{GS} = 0$	$R_{ds  on}$	<	30	60	100	Ω
Feedback capacitance at f = 1 MHz						
$-V_{GS} = 12 \text{ V}; V_{DS} = 0$	$C_{rs}$	<	3.5	3.5	3.5	pF
Turn-off time						
$V_{DD} = 10 \text{ V}; V_{GS} = 0$						
$I_D = 12 \text{ mA}; -V_{GSM} = 12 \text{ V}$	$t_{\text{off}}$	<	20	_	_	ns
$I_D = 6 \text{ mA}; -V_{GSM} = 7 \text{ V}$	$t_{\text{off}}$	<	_	35	_	ns
$I_D = 3 \text{ mA}; -V_{GSM} = 5 \text{ V}$	$t_{off}$	<	_	_	50	ns

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DATINGS								
RATINGS Limiting values in ac	cordance with the Absolute Max	rimum System (	IEC 13	34)				
Drain-source voltag				/ <sub>DS</sub>	max.	40	V	
Drain-source voltage  Drain-gate voltage			± VDS V <sub>DGO</sub>		max.	40		
Gate-source voltage			-V <sub>GSO</sub>		max.	40		
Gate current (DC)	-			000	max.		mA	
, ,	tion up to T <sub>amb</sub> = 40 °C <sup>(1)</sup>		I <sub>G</sub> P <sub>to</sub>	nt	max.		mW	
Storage temperatur			Tsi		-65 to + 150			
	unction temperature T <sub>j</sub>			-9	max.	150	°C	
THERMAL RESISTA	ANCE							
From junction to an	nbient <sup>(1)</sup>		Rtl	h j-a	=	430	K/W	
CHARACTERISTIC								
$T_j = 25$ °C unless oth								
Gate-source voltage				.,				
$I_G = 1 \text{ mA}; V_{DS} = 0$				$V_{GSon}$	<		1	V
Gate-source cut-off							0.4	- 4
$V_{DS} = 0 \text{ V}; -V_{GS}$				-I <sub>GSS</sub>	<		0.1	nA A
$V_{DS} = 0 V; -V_{GS}$	$V_{GS} = 20 \text{ V}; T_{amb} = 150 ^{\circ}\text{C}$		<		0.2	μΑ		
			PME	3F4391	PMBF43		PMBF	
Drain current V <sub>DS</sub> = 20 V; V <sub>GS</sub>	= 0	I <sub>DSS</sub>	> <	50 150	PMBF43	9 <b>2</b> 25 75	5 30	mA mA
		I <sub>DSS</sub>	>	50	PMBF43	25	5	mA
$V_{DS} = 20 \text{ V}; V_{GS}$	down voltage	I <sub>DSS</sub> -V <sub>(BR)GSS</sub>	>	50	PMBF43	25	5	mA
$V_{DS} = 20 \text{ V}; V_{GS}$ Gate-source breake	down voltage - 0		> <	50 150 40 4	PMBF43	25 75 40 2	5 30 40 0.5	mA mA
$V_{DS} = 20 \text{ V}; V_{GS}$ Gate-source breako $-I_G = 1 \mu A; V_{DS} = 1 \mu $	down voltage = 0 voltage	−V <sub>(BR)</sub> GSS	> <	50 150	PMBF43	25 75 40	5 30 40	mA mA
$V_{DS}$ = 20 V; $V_{GS}$ Gate-source breakor $-I_G$ = 1 $\mu$ A; $V_{DS}$ =  Gate-source cut-off $I_D$ = 1 nA; $V_{DS}$ =	down voltage = 0 voltage 20 V se (on)	−V <sub>(BR)</sub> GSS −V <sub>(P)</sub> GS	> < < > > > > > > > > > > > > > > > > >	50 150 40 4 10	PMBF43	25 75 40 2	5 30 40 0.5	mA mA
$V_{DS}$ = 20 V; $V_{GS}$ Gate-source breakor $-I_G$ = 1 $\mu$ A; $V_{DS}$ =  Gate-source cut-off $I_D$ = 1 nA; $V_{DS}$ =  Drain-source voltage $I_D$ = 12 mA; $V_{GS}$ =	down voltage = 0 voltage 20 V ne (on) = 0	$-V_{(BR)GSS}$ $-V_{(P)GS}$ $V_{DSon}$	> < < > > > > > > > > > > > > > > > > >	50 150 40 4	PMBF43	25 75 40 2 5	5 30 40 0.5	mA mA
$V_{DS}$ = 20 V; $V_{GS}$ Gate-source breaks $-I_G$ = 1 $\mu$ A; $V_{DS}$ = Gate-source cut-off $I_D$ = 1 nA; $V_{DS}$ = Drain-source voltag $I_D$ = 12 mA; $V_{GS}$ = $I_D$ = 6 mA; $V_{GS}$ =	down voltage = 0 voltage 20 V e (on) = 0	-V <sub>(BR)</sub> GSS -V <sub>(P)</sub> GS V <sub>DSon</sub> V <sub>DSon</sub>	> < > > <	50 150 40 4 10	PMBF43	25 75 40 2	5 30 40 0.5 3	mA mA V V V
$V_{DS}$ = 20 V; $V_{GS}$ Gate-source break( $-I_G$ = 1 $\mu$ A; $V_{DS}$ =  Gate-source cut-off $I_D$ = 1 nA; $V_{DS}$ =  Drain-source voltage $I_D$ = 12 mA; $V_{GS}$ = $I_D$ = 6 mA; $V_{GS}$ = $I_D$ = 3 mA; $V_{GS}$ =	down voltage = 0 voltage 20 V  se (on) = 0 0	$-V_{(BR)GSS}$ $-V_{(P)GS}$ $V_{DSon}$	> < < > < < < < < < < < < < < < < < < <	50 150 40 4 10	PMBF43	25 75 40 2 5	5 30 40 0.5	mA mA
$V_{DS}$ = 20 V; $V_{GS}$ Gate-source breaks $-I_G$ = 1 $\mu$ A; $V_{DS}$ =  Gate-source cut-off $I_D$ = 1 nA; $V_{DS}$ =  Drain-source voltag $I_D$ = 12 mA; $V_{GS}$ = $I_D$ = 6 mA; $V_{GS}$ = $I_D$ = 3 mA; $V_{GS}$ =  Drain-source resists	down voltage = 0 voltage 20 V  e (on) = 0 0 0 ance (on)	-V <sub>(BR)GSS</sub> -V <sub>(P)GS</sub> V <sub>DSon</sub> V <sub>DSon</sub> V <sub>DSon</sub>	> < < > < < < < < < < < < < < < < < < <	50 150 40 4 10 0.4	PMBF43	25 75 40 2 5	5 30 40 0.5 3	mA mA V V V V
$V_{DS}$ = 20 V; $V_{GS}$ Gate-source break( $-I_G$ = 1 $\mu$ A; $V_{DS}$ =  Gate-source cut-off $I_D$ = 1 nA; $V_{DS}$ =  Drain-source voltage $I_D$ = 12 mA; $V_{GS}$ = $I_D$ = 6 mA; $V_{GS}$ = $I_D$ = 3 mA; $V_{GS}$ =  Drain-source resists $I_D$ = 0; $V_{GS}$ = 0; f	down voltage = 0 voltage 20 V  se (on) = 0 0 0 ance (on) = 1 kHz; T <sub>amb</sub> = 25 °C	-V <sub>(BR)</sub> GSS -V <sub>(P)</sub> GS V <sub>DSon</sub> V <sub>DSon</sub>	> < > < < < < < < < < < < < < < < < < <	50 150 40 4 10	PMBF43	25 75 40 2 5	5 30 40 0.5 3	mA mA V V V
$V_{DS}$ = 20 V; $V_{GS}$ Gate-source breaks $-I_G$ = 1 $\mu$ A; $V_{DS}$ =  Gate-source cut-off $I_D$ = 1 $\mu$ A; $V_{DS}$ =  Drain-source voltag $I_D$ = 12 $\mu$ A; $V_{GS}$ = $I_D$ = 6 $\mu$ A; $V_{GS}$ = $I_D$ = 3 $\mu$ A; $V_{GS}$ =  Drain-source resistat $I_D$ = 0; $V_{GS}$ = 0; f  Drain cut-off current	down voltage = 0 voltage 20 V  ee (on) = 0 0 0 ance (on) = 1 kHz; T <sub>amb</sub> = 25 °C t	-V <sub>(BR)GSS</sub> -V <sub>(P)GS</sub> V <sub>DSon</sub> V <sub>DSon</sub> V <sub>DSon</sub> r <sub>ds on</sub>	> <	50 150 40 4 10 0.4 -	PMBF43	25 75 40 2 5	5 30 40 0.5 3	mA mA V V V V
$V_{DS}$ = 20 V; $V_{GS}$ Gate-source breaks $-I_G$ = 1 $\mu$ A; $V_{DS}$ =  Gate-source cut-off $I_D$ = 1 $n$ A; $V_{DS}$ =  Drain-source voltage $I_D$ = 12 $m$ A; $V_{GS}$ = $I_D$ = 6 $m$ A; $V_{GS}$ = $I_D$ = 3 $m$ A; $V_{GS}$ =  Drain-source resists $I_D$ = 0; $V_{GS}$ = 0; f  Drain cut-off curren $-V_{GS}$ = 12 V	down voltage = 0 voltage 20 V  se (on) = 0 0 0 ance (on) = 1 kHz; T <sub>amb</sub> = 25 °C	-V <sub>(BR)GSS</sub> -V <sub>(P)GS</sub> V <sub>DSon</sub> V <sub>DSon</sub> V <sub>DSon</sub> r <sub>ds on</sub>	>	50 150 40 4 10 0.4	PMBF43	25 75 40 2 5 - 0.4 -	5 30 40 0.5 3 - - 0.4 100	mA mA V V V V V
$V_{DS}$ = 20 V; $V_{GS}$ Gate-source break( $-I_G$ = 1 $\mu$ A; $V_{DS}$ =  Gate-source cut-off $I_D$ = 1 nA; $V_{DS}$ =  Drain-source voltage $I_D$ = 12 mA; $V_{GS}$ = $I_D$ = 6 mA; $V_{GS}$ = $I_D$ = 3 mA; $V_{GS}$ =  Drain-source resistate $I_D$ = 0; $V_{GS}$ = 0; f  Drain cut-off current $-V_{GS}$ = 12 V $-V_{GS}$ = 7 V	down voltage = 0 voltage 20 V  ee (on) = 0 0 0 ance (on) = 1 kHz; T <sub>amb</sub> = 25 °C t	-V <sub>(BR)GSS</sub> -V <sub>(P)GS</sub> V <sub>DSon</sub> V <sub>DSon</sub> V <sub>DSon</sub> I <sub>DSX</sub> I <sub>DSX</sub>	>	50 150 40 4 10 0.4 - 30 0.1 -	PMBF43	25 75 40 2 5	5 30 40 0.5 3 - - 0.4 100	mA mA V V V V V V
$V_{DS}$ = 20 V; $V_{GS}$ Gate-source breaks $-I_G$ = 1 $\mu$ A; $V_{DS}$ =  Gate-source cut-off $I_D$ = 1 $n$ A; $V_{DS}$ =  Drain-source voltag $I_D$ = 12 $m$ A; $V_{GS}$ = $I_D$ = 6 $m$ A; $V_{GS}$ = $I_D$ = 3 $m$ A; $V_{GS}$ =  Drain-source resists $I_D$ = 0; $V_{GS}$ = 0; f  Drain cut-off curren $-V_{GS}$ = 12 V $-V_{GS}$ = 7 V $-V_{GS}$ = 5 V	down voltage = 0 voltage 20 V  se (on) = 0 0 0 ance (on) = 1 kHz; T <sub>amb</sub> = 25 °C t V <sub>DS</sub> = 20 V	-V <sub>(BR)GSS</sub> -V <sub>(P)GS</sub> V <sub>DSon</sub> V <sub>DSon</sub> V <sub>DSon</sub> I <sub>DSX</sub> I <sub>DSX</sub> I <sub>DSX</sub>	>	50 150 40 4 10 0.4 - 30 0.1 - -	PMBF43	25 75 40 2 5 - 0.4 -	5 30 40 0.5 3 - - 0.4 100 - - 0.1	mA mA V V V V V V T Ω
$V_{DS} = 20 \text{ V; } V_{GS}$ $Gate\text{-source break}$ $-I_G = 1  \mu\text{A; } V_{DS} = 0$ $Gate\text{-source cut-off}$ $I_D = 1  n\text{A; } V_{DS} = 0$ $Drain\text{-source voltag}$ $I_D = 12 \text{ mA; } V_{GS} = 0$ $I_D = 12  m$	down voltage = 0 voltage 20 V  ee (on) = 0 0 0 ance (on) = 1 kHz; T <sub>amb</sub> = 25 °C t	-V(BR)GSS -V(P)GS  VDSon VDSon VDSon IDSX IDSX IDSX IDSX IDSX	>	50 150 40 4 10 0.4 - 30 0.1 - - 0.2	PMBF43	25 75 40 2 5 - 0.4 - - - 0.1	5 30 40 0.5 3 - - 0.4 100 - - 0.1	mA mA V V V V V V V A nA nA nA μA
$V_{DS}$ = 20 V; $V_{GS}$ Gate-source breaks $-I_G$ = 1 $\mu$ A; $V_{DS}$ =  Gate-source cut-off $I_D$ = 1 $n$ A; $V_{DS}$ =  Drain-source voltag $I_D$ = 12 $m$ A; $V_{GS}$ = $I_D$ = 6 $m$ A; $V_{GS}$ = $I_D$ = 3 $m$ A; $V_{GS}$ =  Drain-source resists $I_D$ = 0; $V_{GS}$ = 0; f  Drain cut-off curren $-V_{GS}$ = 12 V $-V_{GS}$ = 7 V $-V_{GS}$ = 5 V	down voltage = 0 voltage 20 V  se (on) = 0 0 0 ance (on) = 1 kHz; T <sub>amb</sub> = 25 °C t V <sub>DS</sub> = 20 V	-V <sub>(BR)GSS</sub> -V <sub>(P)GS</sub> V <sub>DSon</sub> V <sub>DSon</sub> V <sub>DSon</sub> I <sub>DSX</sub> I <sub>DSX</sub> I <sub>DSX</sub>	>	50 150 40 4 10 0.4 - 30 0.1 - -	PMBF43	25 75 40 2 5 - 0.4 -	5 30 40 0.5 3 - - 0.4 100 - - 0.1	mA mA V V V V V V T Ω

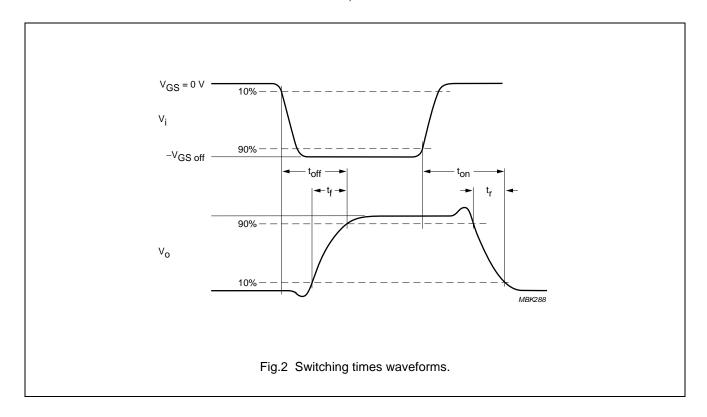
# N-channel FETs

PMBF4391; PMBF4392; PMBF4393

y-parameters (common source)						
$V_{DS}$ = 20 V; $V_{GS}$ = 0; f = 1 MHz; $T_{amb}$ = 25 °C		PMBF4391		PMBF4392	PMBF4393	
Input capacitance	$C_{is}$	<	14	14	14	pF
Feedback capacitance						
$-V_{GS} = 12 \text{ V}$ ; $V_{DS} = 0$	$C_{rs}$	<	3.5	_	_	pF
$-V_{GS} = 7 V$ ; $V_{DS} = 0$	$C_{rs}$	<	_	3.5	_	pF
$-V_{GS} = 5 V$ ; $V_{DS} = 0$	$C_{rs}$	<	_	_	3.5	pF
Switching times						
$V_{DD} = 10 \text{ V}$ ; $V_{DS} = 0$						
Conditions I <sub>D</sub> and -V <sub>GSoff</sub>	$I_D$	=	12	6	3	mA
	$-V_{GS\ off}$	=	12	7	5	V
	$R_L$	=	750	1550	3150	Ω
Rise time	t <sub>r</sub>	<	5	5	5	ns
Turn on time	t <sub>on</sub>	<	15	15	15	ns
Fall time	t <sub>f</sub>	<	15	20	30	ns
Turn off time	$t_{\text{off}}$	<	20	35	50	ns

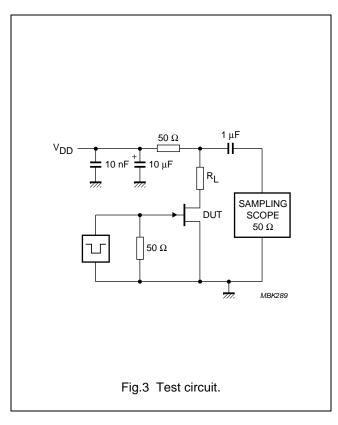
# Note

1. Mounted on a ceramic substrate of 8 mm  $\times$  10 mm  $\times$  0,7 mm.



# N-channel FETs

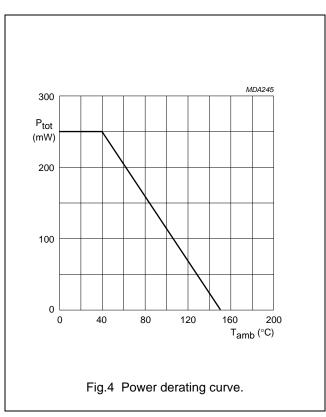
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# Pulse generator:

0.5 ns 0.5 ns <  $100~\mu s$ 0.01 Oscilloscope:

 $R_{i}$ 50  $\Omega$ 



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# N-channel FETs

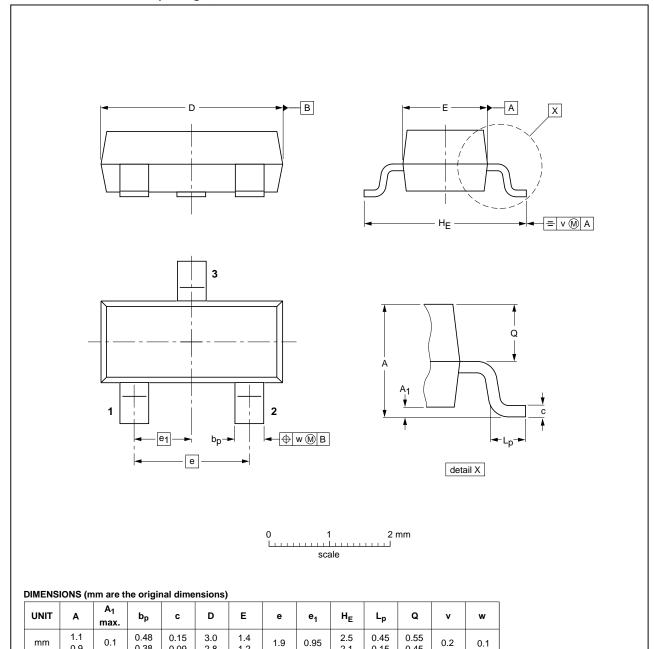
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PMBF4393

# **PACKAGE OUTLINE**

# Plastic surface-mounted package; 3 leads

SOT23



OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	1330E DATE
SOT23		TO-236AB				<del>04-11-04</del> 06-03-16

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0.38

Downloaded from Arrow.com.

0.9

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### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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provides High Performance Mixed Signal and Standard Product solutions that leverage its leading RF, Analog, Power Management, Interface, Security and Digital Processing expertise

### **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

### **Contact information**

For additional information please visit: http://www.nxp.com
For sales offices addresses send e-mail to: salesaddresses@nxp.com

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